

NTE379 Silicon NPN Transistor Power Amp, High Voltage, Switch

Description:

The NTE379 is a silicon NPN transistor in a TO220 type package designed for high-voltage, high-speed power switching inductive circuits where fall time is critical. This device is particularly suited for 115 and 220V switch-mode applications such as Switching Regulators, Inverters, Motor Controls, Solenoid/Relay drivers, and Deflection circuits.

Features:

- $V_{CEO(sus)} = 400V$
- Reverse Bias SOA with Inductive Loads @ $T_C = +100^\circ C$
- 700V Blocking Capability

Absolute Maximum Ratings:

Collector–Emitter Voltage, $V_{CEO(sus)}$	400V
Collector–Emitter Voltage, V_{CEV}	700V
Emitter–Base Voltage, V_{EBO}	9V
Collector Current, I_C	
Continuous	12A
Peak (Note 1)	24A
Base Current, I_B	
Continuous	6A
Peak (Note 1)	12A
Emitter Current, I_E	
Continuous	18A
Peak (Note 1)	36A
Total Power Dissipation ($T_A = +25^\circ C$), P_D	2W
Derate Above $25^\circ C$	16mW/ $^\circ C$
Total Power Dissipation ($T_C = +25^\circ C$), P_D	100W
Derate Above $25^\circ C$	800mW/ $^\circ C$
Operating Junction Temperature Range, T_J	-65° to $+150^\circ C$
Storage Temperature Range, T_{stg}	-65° to $+150^\circ C$
Thermal Resistance, Junction to Case, R_{thJC}	1.25 $^\circ C/W$
Thermal Resistance, Junction to Ambient, R_{thJA}	62.5 $^\circ C/W$
Lead Temperature (During Soldering, 1/8" from case for 5sec), T_L	$+275^\circ C$

Note 1. Pulse Test: Pulse Width = 5ms, Duty Cycle \leq 10%.

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics (Note 2)						
Collector–Emitter Sustaining Voltage	$V_{\text{CEO(sus)}}$	$I_C = 10\text{mA}, I_B = 0$	400	–	–	V
Collector Cutoff Current	I_{CEV}	$V_{\text{CEV}} = 700\text{V}, V_{\text{BE(off)}} = 1.5\text{V}$	–	–	1	mA
		$V_{\text{CEV}} = 700\text{V}, V_{\text{BE(off)}} = 1.5\text{V}, T_C = +100^\circ\text{C}$	–	–	5	mA
Emitter Cutoff Current	I_{EBO}	$V_{\text{EB}} = 9\text{V}, I_C = 0$	–	–	1	mA
ON Characteristics (Note 2)						
DC Current Gain	h_{FE}	$I_C = 5\text{A}, V_{\text{CE}} = 5\text{V}$	8	–	40	
		$I_C = 8\text{A}, V_{\text{CE}} = 5\text{V}$	6	–	30	
Collector–Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_C = 5\text{A}, I_B = 1\text{A}$	–	–	1.0	V
		$I_C = 8\text{A}, I_B = 1.6\text{A}$	–	–	1.5	V
		$I_C = 12\text{A}, I_B = 3\text{A}$	–	–	3.0	V
		$I_C = 8\text{A}, I_B = 1.6\text{A}, T_C = +100^\circ\text{C}$	–	–	2.0	V
Base–Emitter Saturation Voltage	$V_{\text{BE(sat)}}$	$I_C = 5\text{A}, I_B = 1\text{A}$	–	–	1.2	V
		$I_C = 8\text{A}, I_B = 1.6\text{A}$	–	–	1.6	V
		$I_C = 8\text{A}, I_B = 1.6\text{A}, T_C = +100^\circ\text{C}$	–	–	1.5	V
Dynamic Characteristics						
Current Gain–Bandwidth Product	f_T	$I_C = 500\text{mA}, V_{\text{CE}} = 10\text{V}, f = 1\text{MHz}$	4	–	–	MHz
Output Capacitance	C_{ob}	$V_{\text{CB}} = 10\text{V}, I_E = 0, f = 0.1\text{MHz}$	–	180	–	pF
Switching Characteristics						
Resistive Load						
Delay Time	t_d	$V_{\text{CC}} = 125\text{V}, I_C = 8\text{A}, I_{\text{B1}} = I_{\text{B2}} = 1.6\text{A}, t_p = 25\mu\text{s}, \text{Duty Cycle} \leq 1\%$	–	0.06	0.1	μs
Rise Time	t_r		–	0.45	1.0	μs
Storage Time	t_s		–	1.3	3.0	μs
Fall Time	t_f		–	0.2	0.7	μs
Inductive Load, Clamped						
Voltage Storage Time	t_{sv}	$I_C = 8\text{A}, V_{\text{clamp}} = 300\text{V}, I_{\text{B1}} = 1.6\text{A}, V_{\text{BE(off)}} = 5\text{V}, T_C = +100^\circ\text{C}$	–	0.92	2.3	μs
Crossover Time	t_c		–	0.12	0.7	μs

Note 2. Pulse Test: Pulse Width = $300\mu\text{s}$, Duty Cycle = 2%.

